KTD1302

Rev.E Mar.-2016

DATA SHEET

TO-92 NPN Silicon NPN transistor in a TO-92 Plastic Package.

:R_{on}=0.6Ω(Typ.)(I_B=1.0mA)

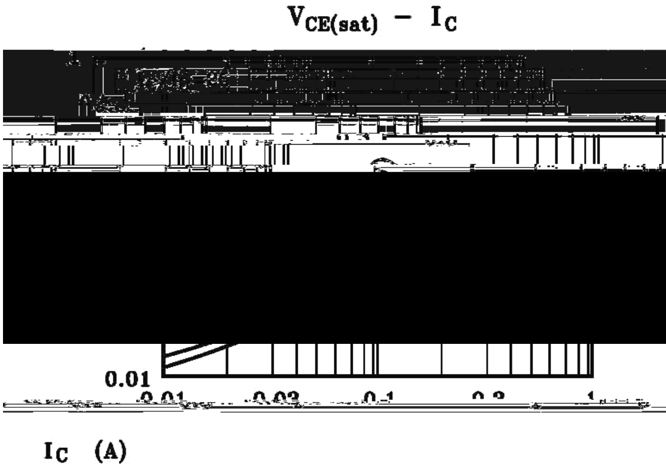
Low on Resistance: R_{on}=0.6Ω(Typ.)(I_B=1.0mA).

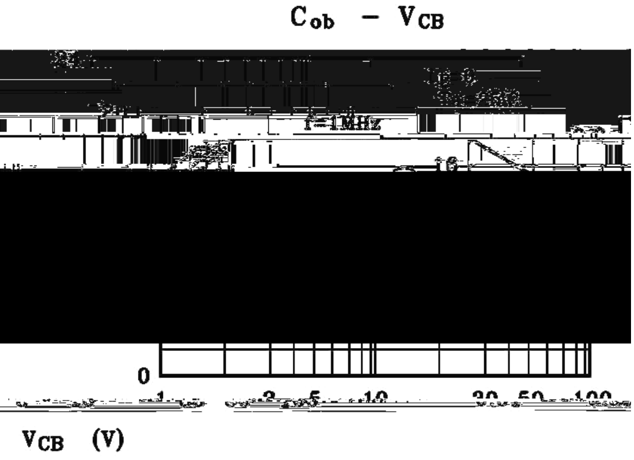
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CB0}	25	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	9.0	V
Collector Current - Continuous	I_C	300	mA
Base Current – Continuous	I_B	30	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55˙ 150	

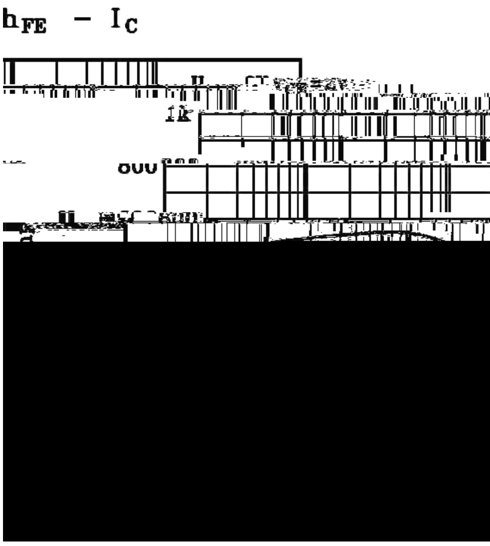
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=25V I_E=0			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=9.0V I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=2.0V I_C=4.0mA	200		800	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=100mA I_B=10mA			0.25	V

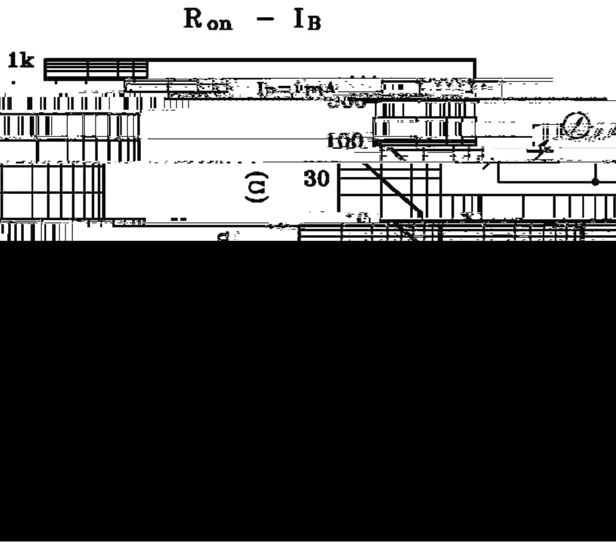
[redacted]

/ Electrical Characteristic Curve


$V_{CE(sat)}$ − I_C

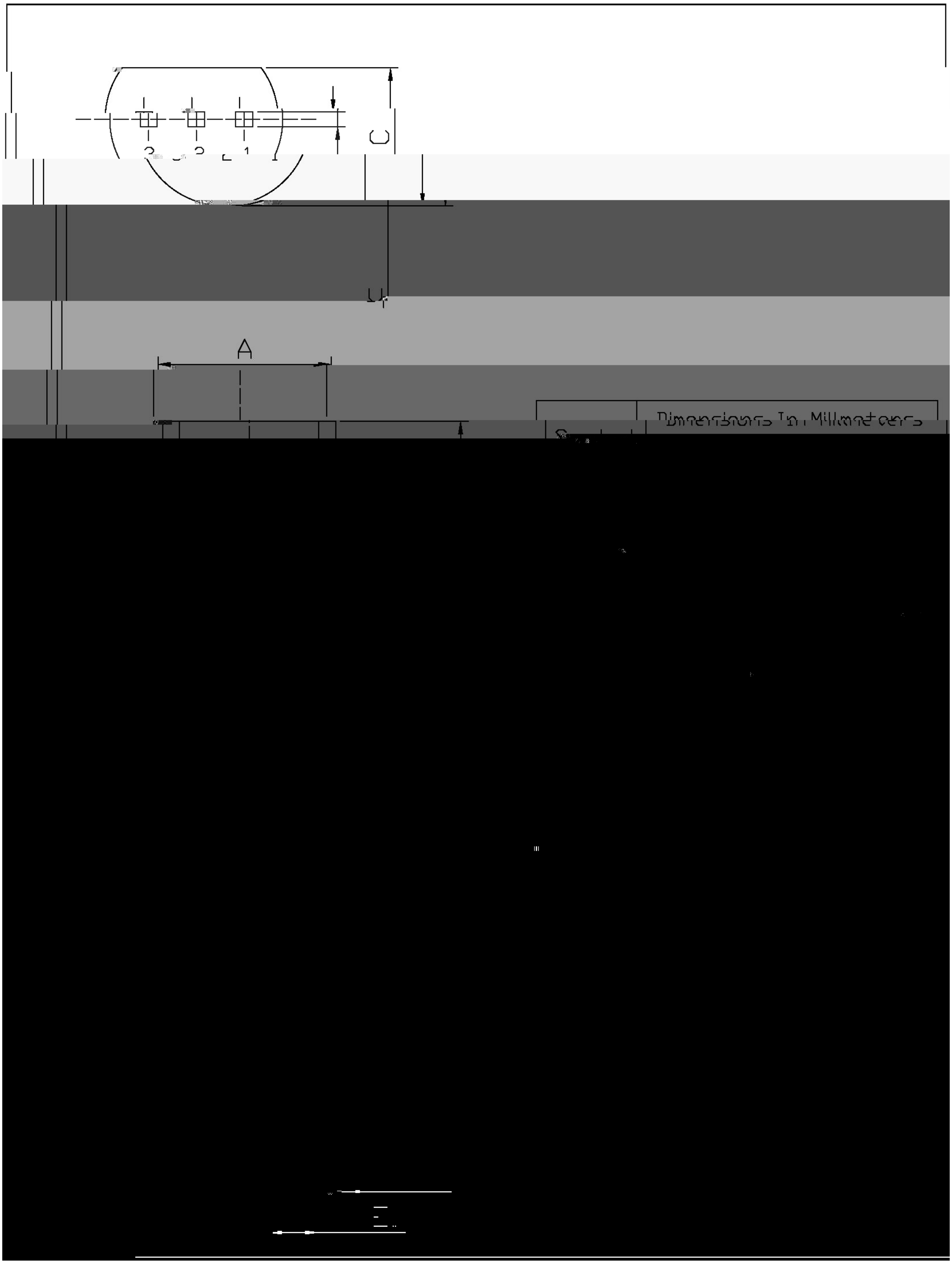

C_{ob} − V_{CB}


h_{FE} − I_C

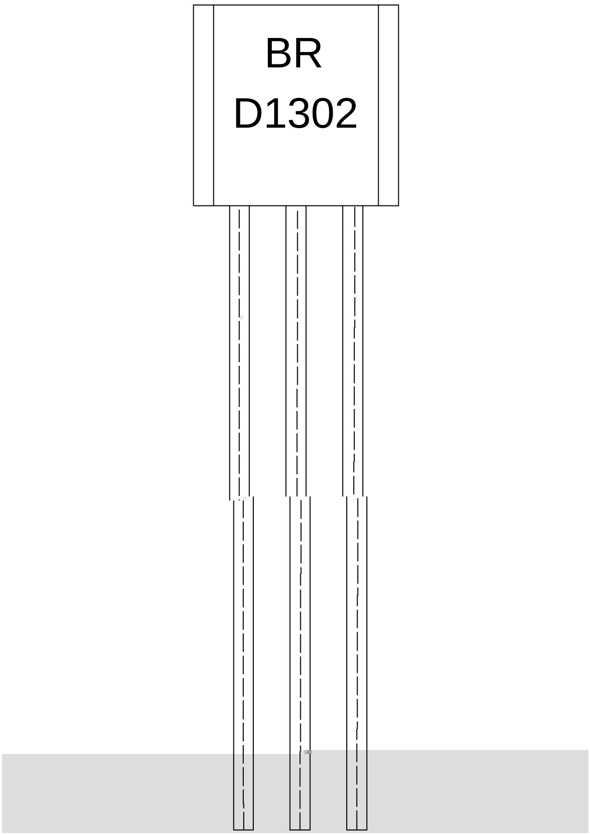

R_{on} − I_B

/ Package Dimensions

TO-92 Unit: mm



/ Marking Instructions



BR:

D1302

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Note:

BR:	Company Code.
D1302:	Product Type.
****:	Lot No. Code,code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)

1 25 150 60 90sec;
2 255±5 5±0.5sec;
3 2 10 /sec.

Note:
1.Preheating:25~150 , Time:60~90sec.
2.Peak Temp.:255±5 , Duration:5±0.5sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec.

Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)		
	只 袋	袋 盒	只 盒	盒 箱	只 箱	袋	盒	箱

/ AMMO

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm3)	
	只 纸带	纸带 盒	纸带层 盒	盒 箱	只 箱	盒	箱
							小箱 , 大箱

/ Notices